December 2013

FQP8N80C / FQPF8N80C / FQPF8N80CYDTU

N-Channel QFET® MOSFET

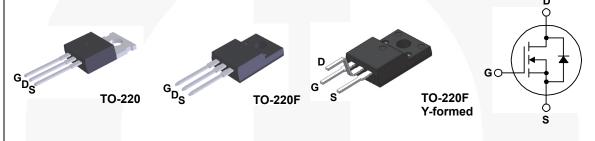
800 V, 8.0 A, 1.55 Ω

Description

This N-Channel enhancement mode power MOSFET is • 8.0 A, 800 V, $R_{DS(on)}$ = 1.55 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 35 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 13 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 4.0 A$



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FQP8N80C	FQP8N80C FQPF8N80C	
V _{DSS}	Drain-Source Voltage	800		V
I _D	Drain Current - Continuous (T _C = 25°C)	8	8 *	Α
	- Continuous (T _C = 100°C)	5.1	5.1 *	Α
I _{DM}	Drain Current - Pulsed (Note 1)	32	32 *	Α
V _{GSS}	Gate-Source Voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	850		mJ
I _{AR}	Avalanche Current (Note 1)	8		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)	17.8		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_{D}	Power Dissipation (T _C = 25°C)	178	59	W
	- Derate above 25°C	1.43	0.48	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	3	00	°C

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP8N80C	FQPF8N80C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.89	2.66	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP8N80C	FQP8N80C	TO-220	Tube	N/A	N/A	50 units
FQPF8N80C	FQPF8N80C	TO-220F	Tube	N/A	N/A	50 units
FQPF8N80CYDTU	FQPF8N80C	TO-220F (Y-formed)	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		0.5	1	V/°(
I _{DSS}	Zana Cata Valtana Brain Cumant	ve Voltage Drain Current $ \frac{V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}}{V_{DS} = 640 \text{ V}, T_{C} = 125^{\circ}\text{C}} $			10	μΑ
	Zero Gate Voltage Drain Current				100	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4 A		1.29	1.55	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 4 A (Note 4)		5.6	-	S
	ic Characteristics			4500	2050	
Ciss	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1580	2050	pF
Coss	Output Capacitance	f = 1.0 MHz		135	175	pF
C _{rss}	Reverse Transfer Capacitance			13	17	pF
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 8 A,		40	90	ns
4 (011)		$V_{DD} = 400 \text{ V}, I_D = 6 \text{ A},$		110	230	ns
t _r	Turn-On Rise Time	$P_{-} = 25.0$				
t _r	Turn-On Rise Time Turn-Off Delay Time	$R_G = 25 \Omega$		65	140	ns
		R_G = 25 Ω (Note 4, 5)			140 150	
t _r t _{d(off)} t _f	Turn-Off Delay Time	(Note 4, 5)		65		ns ns nC
t_{r} $t_{d(off)}$	Turn-Off Delay Time Turn-Off Fall Time			65 70	150	ns

Q_{rr}

 I_{SM}

 V_{SD}

 t_{rr}

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 25 mH, I_{AS} = 8 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} \leq 8 A, di/dt \leq 200 A/ μ s, V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Pulse test : pulse-width \leq 300 μ s, duty cycle \leq 2%. 5. Essentially independent of operating temperature.

Drain-Source Diode Forward Voltage

Maximum Continuous Drain-Source Diode Forward Current

Maximum Pulsed Drain-Source Diode Forward Current

Reverse Recovery Time

Reverse Recovery Charge

8

32

1.4

690

8.2

(Note 4)

Α

Α

V

ns

μС

 V_{GS} = 0 V, I_{S} = 8 A

 $V_{GS} = 0 V, I_{S} = 8 A,$

 $dI_F / dt = 100 A/\mu s$

Typical Characteristics

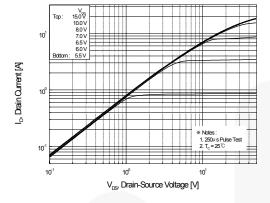


Figure 1. On-Region Characteristics

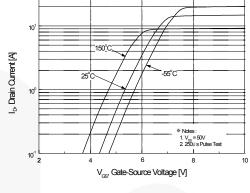


Figure 2. Transfer Characteristics

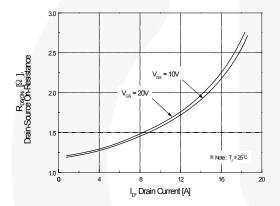


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

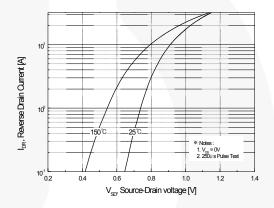


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

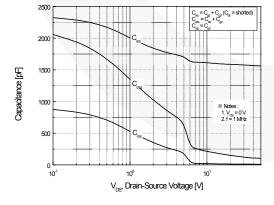


Figure 5. Capacitance Characteristics

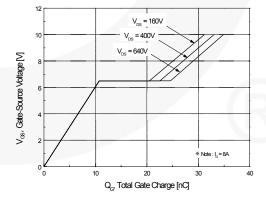


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

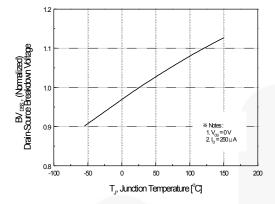


Figure 7. Breakdown Voltage Variation vs Temperature

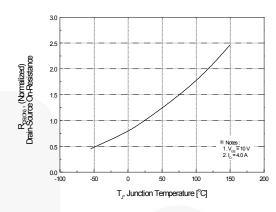


Figure 8. On-Resistance Variation vs Temperature

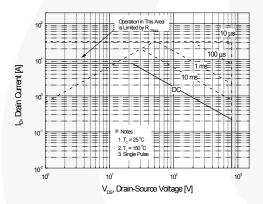


Figure 9-1. Maximum Safe Operating Area for FQP8N80C

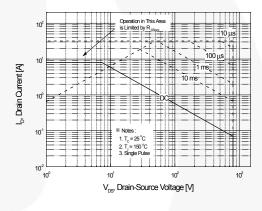


Figure 9-2. Maximum Safe Operating Area for FQPF8N80C

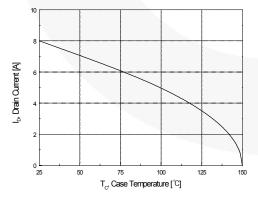


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

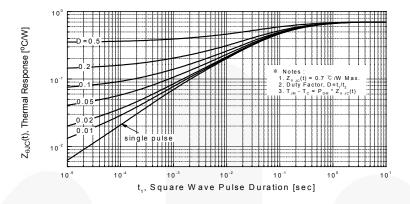


Figure 11-1. Transient Thermal Response Curve for FQP8N80C

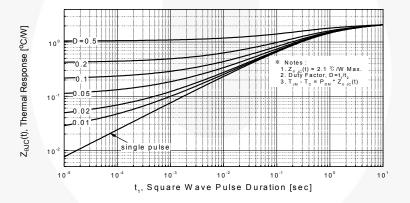


Figure 11-2. Transient Thermal Response Curve for FQPF8N80C

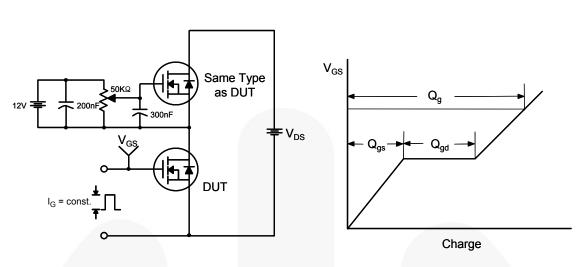


Figure 12. Gate Charge Test Circuit & Waveform

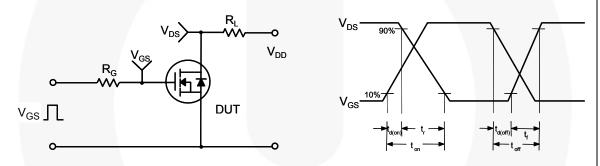


Figure 13. Resistive Switching Test Circuit & Waveforms

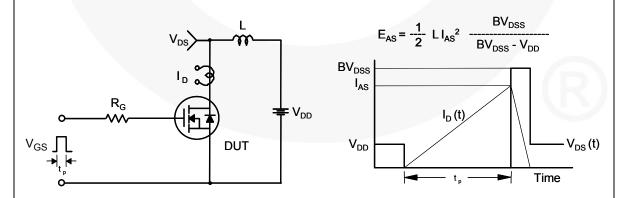
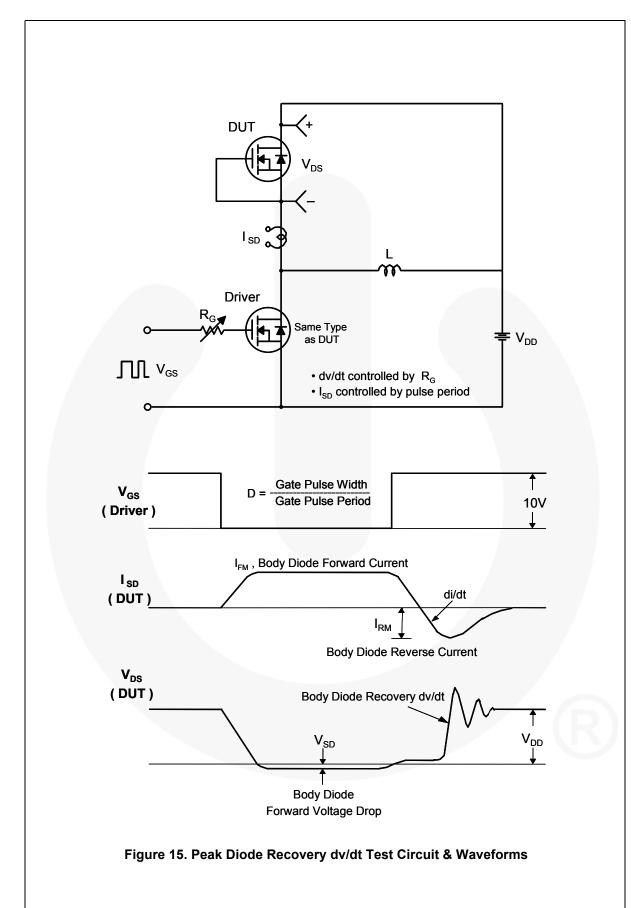


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

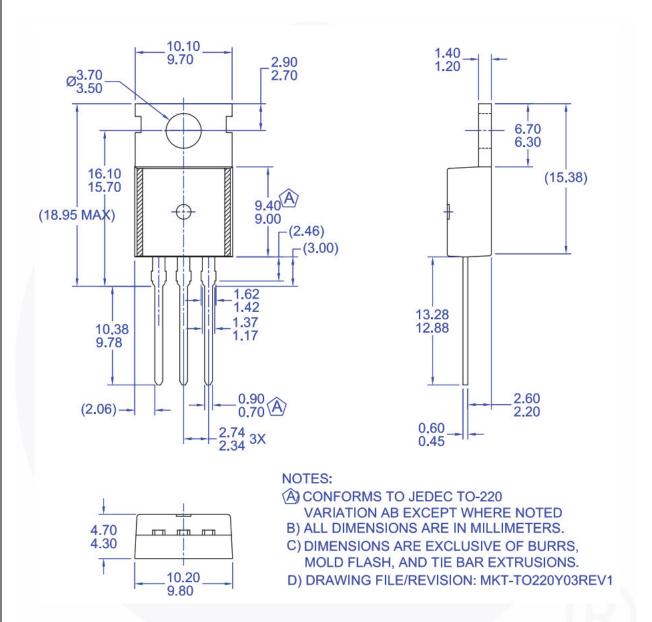


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

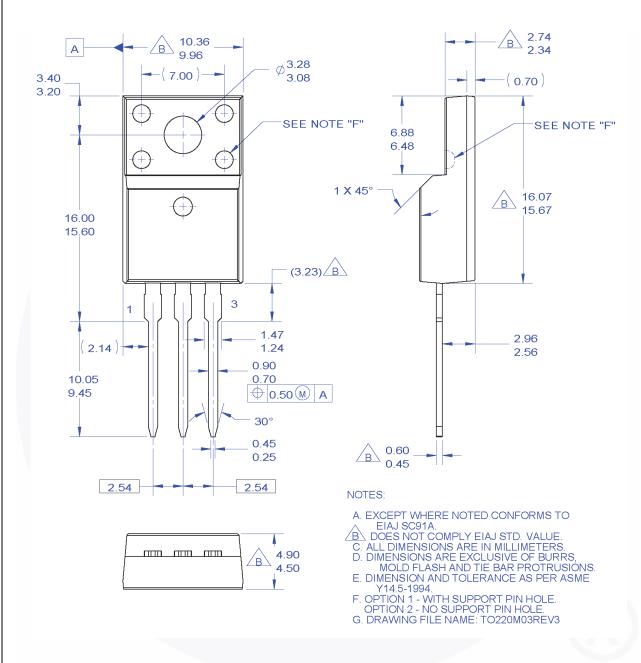


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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Mechanical Dimensions

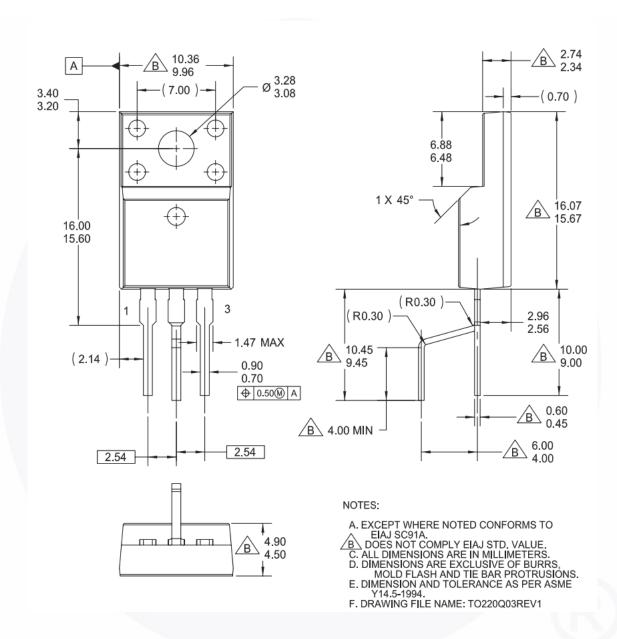


Figure 18. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Y-Formed

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